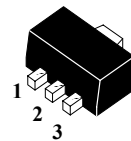


### NPN EPITAXIAL PLANAR TRANSISTOR

 Lead(Pb)-Free

1. BASE  
2. COLLECTOR  
3. EMITTER



**SOT-89**

#### MAXIMUM RATINGS ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Units
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	32	V
Emitter-Base Voltage	$V_{EBO}$	5.0	V
Collector Current -Continuous	$I_C$	2.0	A
Collector Power dissipation	$P_C$	500	mW
Junction Temperature	$T_J$	150	$^{\circ}\text{C}$
Storage Temperature	$T_{stg}$	-55-150	$^{\circ}\text{C}$

#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu\text{A}$ , $I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$ , $I_B=0$	32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu\text{A}$ , $I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=20\text{V}$ , $I_E=0$			1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=4\text{V}$ , $I_C=0$			1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=3\text{V}$ , $I_C=500\text{mA}$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{A}$ , $I_B=0.2\text{A}$			0.8	V
Transition frequency	$f_T$	$V_{CE}=5\text{V}$ , $I_C=50\text{mA}$ , $f=100\text{MHz}$		100		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}$ , $I_E=0$ , $f=1\text{MHz}$		30		pF

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking	DBP	DBQ	DBR

## Typical Characteristics

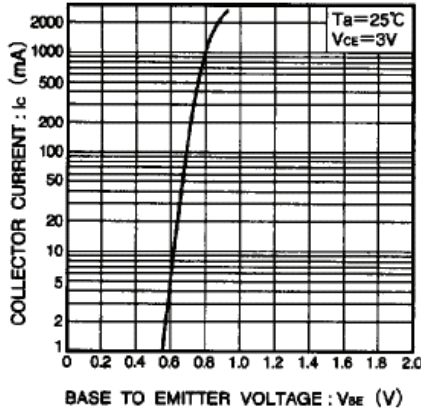


Fig.1 Grounded emitter propagation characteristics

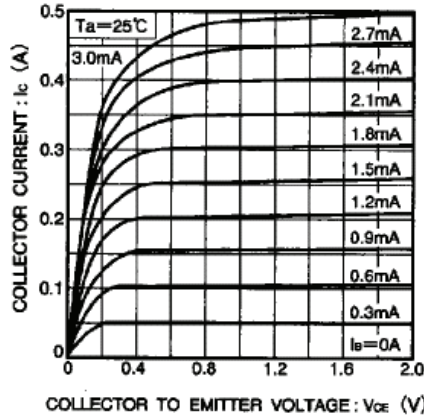


Fig.2 Grounded emitter output characteristics

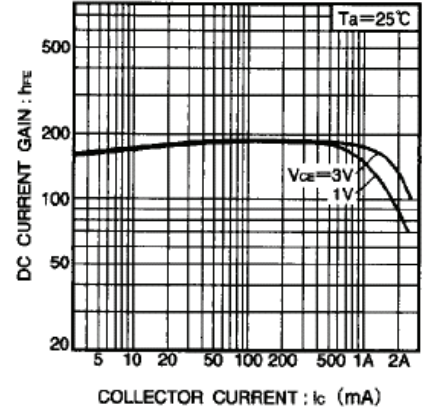


Fig.3 DC current gain vs. collector current

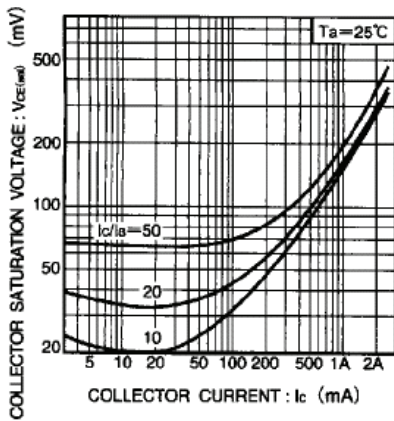


Fig.4 Collector-emitter saturation voltage vs. collector current

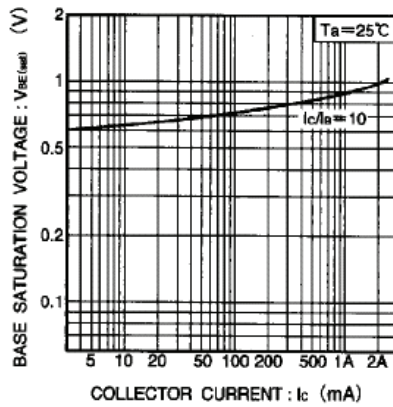


Fig.5 Collector-emitter saturation voltage vs. collector current

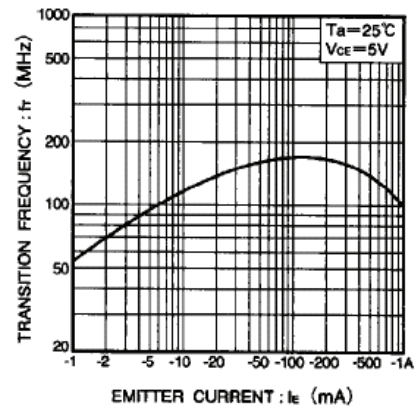


Fig.6 Transition frequency vs. emitter current

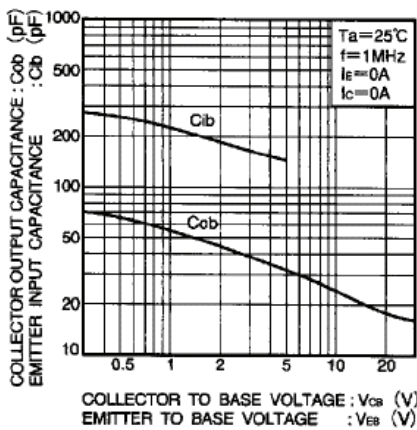


Fig.7 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

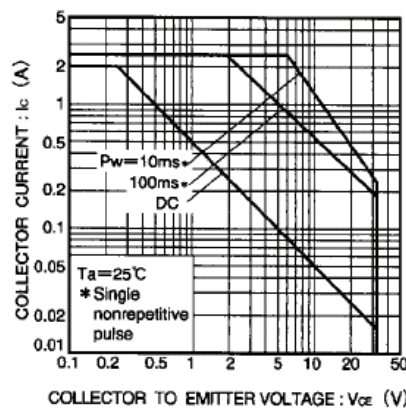
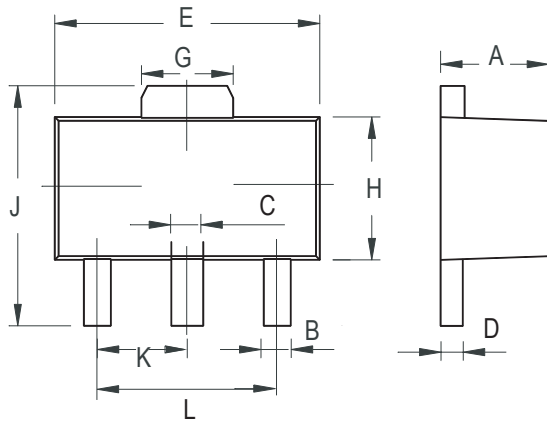


Fig.8 Safe operating area (2SD1766)

**SOT-89 Outline Dimensions**

unit:mm



<b>SOT-89</b>		
<b>Dim</b>	<b>Min</b>	<b>Max</b>
<b>A</b>	1.400	1.600
<b>B</b>	0.320	0.520
<b>C</b>	0.360	0.560
<b>D</b>	0.350	0.440
<b>E</b>	4.400	4.600
<b>G</b>	1.400	1.800
<b>H</b>	2.300	2.600
<b>J</b>	3.940	4.250
<b>K</b>	1.500TYP	
<b>L</b>	2.900	3.100